TO-92 Plastic-Encapsulate Transistors

AV8550 TRANSISTOR（ PNP ）

FEATURES

Power dissipation

P_{CM} : 1 W（Tamb=25℃）

Collector current

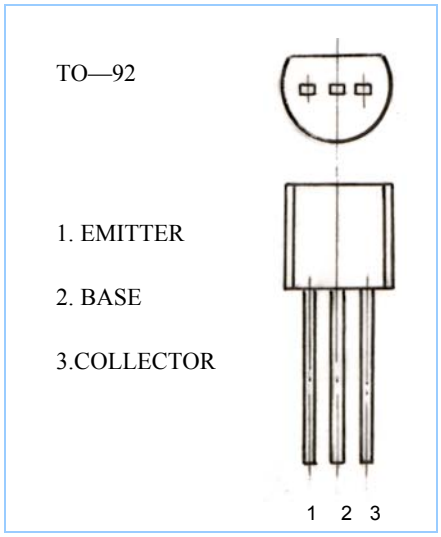
I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J , T_{stg}: -55℃ to +150℃



ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100 μA , I_E=0	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -0.1 mA , I_B=0	-25			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100 μA , I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V , I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20 V , I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V , I_C=0			-0.1	MA
DC current gain	$H_{FE(1)}$	V_{CE}= -1V , I_C=-100 mA	85		300	
	$H_{FE(2)}$	V_{CE}=-1V , I_C=-800 mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-800 m,I_B=-80 mA			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-800mA,I_B=-80 mA			-1.2	V
Base-emitter voltage	V_{BE}	I_E= -1.5A			-1.6	V
Transition frequency	f_T	V_{CE}=-10 V, I_C=-50mA f =30 MHz	190			MHz

CLASSIFICATION OF HFE(1)

Rank	B	C	D
Range	85-160	120-200	160-300

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TYPICAL PERFORMANCE CHARACTERISTICS

Fig.1 Static characteristics

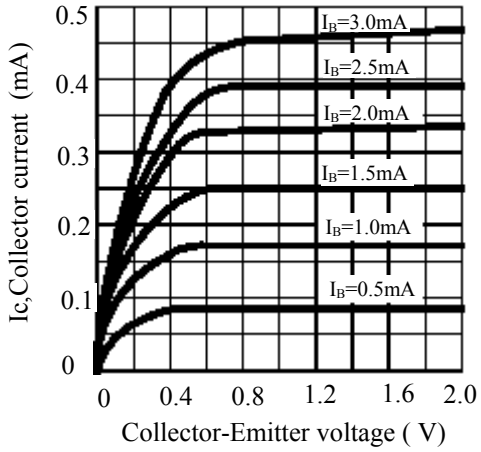

Fig.2 DC current Gain

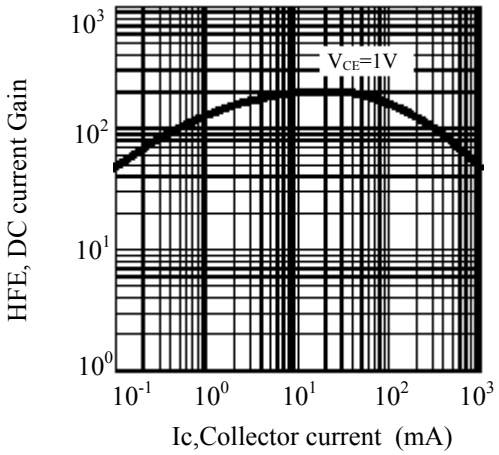

Fig.3 Base-Emitter on Voltage

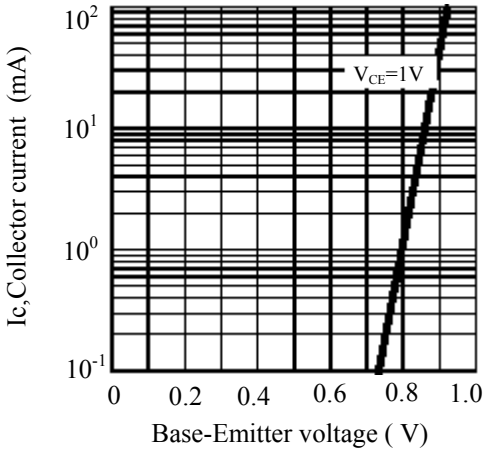

Fig.4 Saturation voltage

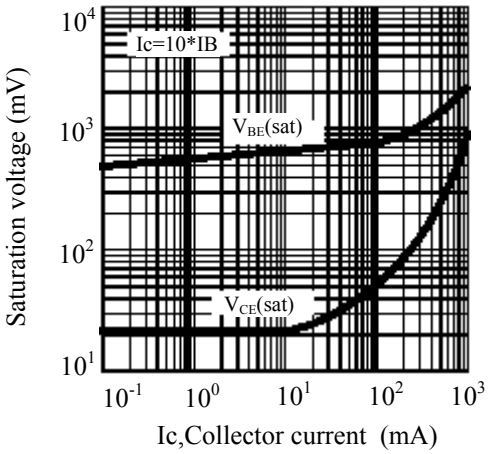

Fig.5 Current gain-bandwidth product

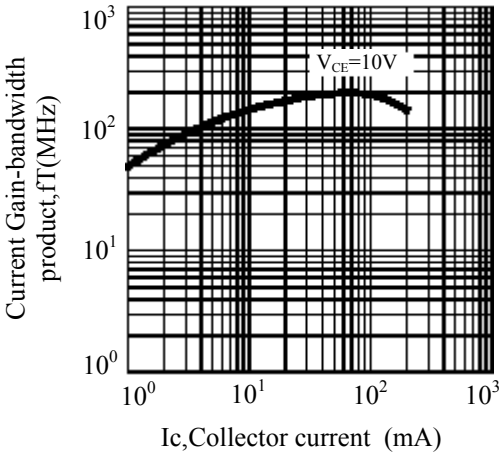

Fig.6 Collector output Capacitance